



Product Overview

HGTG30N60A4: IGBT, 600V, SMPS

For complete documentation, see the data sheet.

The HGTG30N60A4 combines the best features of high input impedance of a MOSFET and the low on-state conduction loss of a bipolar transistor. This IGBT is ideal for many high voltage switching applications operating at high frequencies where low conduction losses are essential. This device has been optimized for fast switching applications, such as UPS and welder.

Features

- 60A, 600V @ TC = 110°C
- Low Saturation Voltage : $V_{CE(sat)} = 1.8\text{ V @ } I_C = 30\text{A}$
- Typical Fall Time. 58ns at $T_J = 125^\circ\text{C}$
- Low Conduction Loss

Applications

- Other Industrial

Part Electrical Specifications																
Product	Compliance	Status	$V_{ES}^{(BR)C}$ Typ (V)	I_C Max (A)	$V_{GE(sat)}$ Typ (V)	V_F Typ (V)	E_{off} Typ (mJ)	E_{on} Typ (mJ)	T_{rr} Typ (ns)	I_{rr} Typ (A)	Gate Charge Typ (nC)	Short Circuit Withstand (μs)	E_{AS} Typ (mJ)	P_D Max (W)	Co- Pack aged Diode	Package Type
HGTG30N60A4	Pb-free	Active	600	60	1.8	-	0.24	0.28	-	-	225	-	-	463	No	TO-247-3

For more information please contact your local sales support at www.onsemi.com.

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